Icemos Technology Ltd Product Specification 1003.121001 Issue Date 20 June 2016 15:59:0

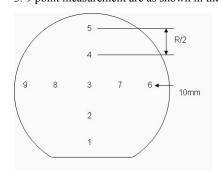
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Part Number	Customer	
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Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110}+/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	400.00 +/- 5.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00μm	Guaranteed by Process
	7.0	Bow	<40.00μm	ADE to ASTM F534, 20%
	8.0	Warp	<40.00μm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	400.00 +/- 5.00 μm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Phosphorous	Wafer Vendor
	16.0	Handle Resistivity	1-10 Ohmem	Wafer Vendor
	17.0	Backside Finish	Polished with no laser marking	Wafer Vendor
DeviceSilicon	18.0	LPD Count	<30.00pces	@0.3um, Tencor 6220 particle counter
	19.0	Scratches	0	Bright Light, 100% (note 2)
	20.0	Haze	none	Bright Light, 100% (note 2)

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Part Number		Customer	
Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspec	tion performed using microscope scan as below. 5x objective.	
		pections performed exclude all wafer area outside the edge exclusion. High intensity bright lamp inspection as per ASTM F523.	ion defined in Overall

3. 9 point measurement are as shown in the diagram below:



Additional Information